

30 V, 1 A PNP/PNP low VCEsat (BISS) transistor 12 December 2012 Pro

**Product data sheet** 

## 1. General description

PNP/PNP low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a leadless medium power DFN2020-6 (SOT1118) Surface-Mounted Device (SMD) plastic package.

NPN/PNP complement: PBSS4130PANP. NPN/NPN complement: PBSS4130PAN.

## 2. Features and benefits

- Very low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability  ${\sf I}_{\sf C}$  and  ${\sf I}_{\sf CM}$
- High collector current gain h<sub>FE</sub> at high I<sub>C</sub>
- Reduced Printed-Circuit Board (PCB) requirements
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

## 3. Applications

- Load switch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

## 4. Quick reference data

Table 1. Quick reference data								
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor								
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	-30	V	
I <sub>C</sub>	collector current			-	-	-1	А	
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-	-2	А	
Per transistor								
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = -1 A; $I_{B}$ = -0.1 A; pulsed; $t_{p} \le 300$ μs; δ $\le 0.02$ ; $T_{amb}$ = 25 °C		-	-	250	mΩ	

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# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	6 5 4	C1 B2 E2
2	B1	base TR1		
3	C2	collector TR2	7 8	
4	E2	emitter TR2		
5	B2	base TR2	1 2 3	E1 B1 C2
6	C1	collector TR1	Transparent top view DFN2020-6 (SOT1118)	sym138
7	C1	collector TR1	21112020 3 (0011110)	
8	C2	collector TR2		

# 6. Ordering information

Table 3. Ordering information							
Type number	Package	kage					
	Name	Description	Version				
PBSS5130PAP	DFN2020-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body $2 \times 2 \times 0.65$ mm	SOT1118				

## 7. Marking

1	Fable 4.   Marking codes	
	Type number	Marking code
	PBSS5130PAP	2E

# 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit				
Per transisto	Per transistor									
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-30	V				
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-30	V				
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-7	V				
I <sub>C</sub>	collector current			-	-1	А				
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$		-	-2	А				
I <sub>B</sub>	base current			-	-0.3	А				
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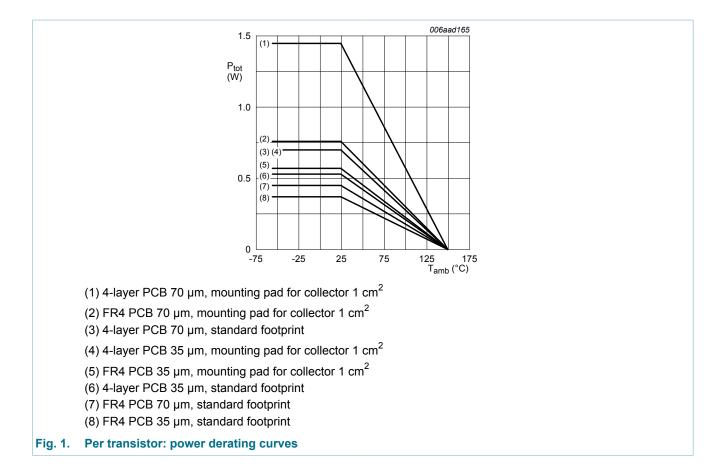
Symbol	Parameter	Conditions	Mi	n Max	Unit
I <sub>BM</sub>	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	-1	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1] -	370	mW
			[2] -	570	mW
			[3] -	530	mW
			[4] -	700	mW
			[5] -	450	mW
			[6] -	760	mW
			[7] -	700	mW
			[8] -	1450	mW
Per device					
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1] -	510	mW
			[2] -	780	mW
			[3] -	730	mW
			[4] -	960	mW
			[5] -	620	mW
			[6] -	1040	mW
			[7] -	960	mW
			[8] -	2000	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-5	5 150	°C
T <sub>stg</sub>	storage temperature		-6	5 150	°C

Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated and standard footprint.
 Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

- [3] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated and standard footprint.
- [4] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [5] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated and standard footprint.
- [6] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [7] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated and standard footprint.
- [8] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

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## 9. Thermal characteristics

Table 6. T	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	tor		· ·				
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	-	338	K/W
	from junction to		[2]	-	-	219	K/W
	ambient		[3]	-	-	236	K/W
			[4]	-	-	179	K/W
			[5]	-	-	278	K/W
			[6]	-	-	164	K/W
			[7]	-	-	179	K/W
			[8]	-	-	86	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	30	K/W

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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Per device			I				
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	-	245	K/W
from jui ambien	from junction to		[2]	-	-	160	K/W
	ampient		[3]	-	-	171	K/W
			[4]	-	-	130	K/W
			[5]	-	-	202	K/W
			[6]	-	-	120	K/W
			[7]	-	-	130	K/W
			[8]	-	-	63	K/W

Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated and standard footprint.
 Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

[3] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated and standard footprint.

<sup>[4]</sup> Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

[5] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated and standard footprint.

[6] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

[7] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated and standard footprint.

[8] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

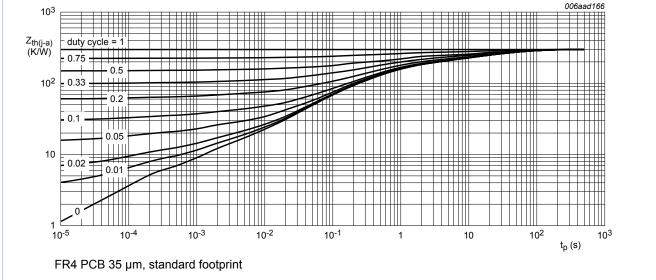
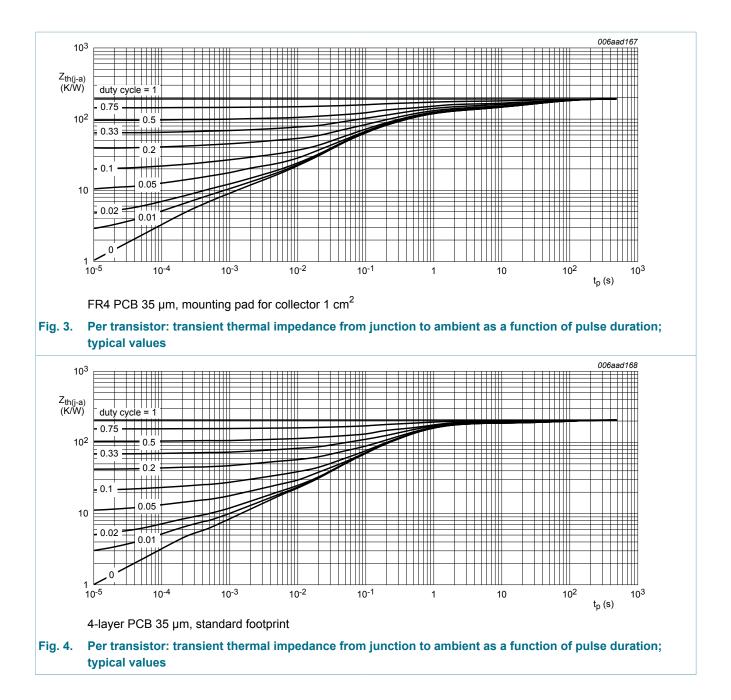


Fig. 2. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values



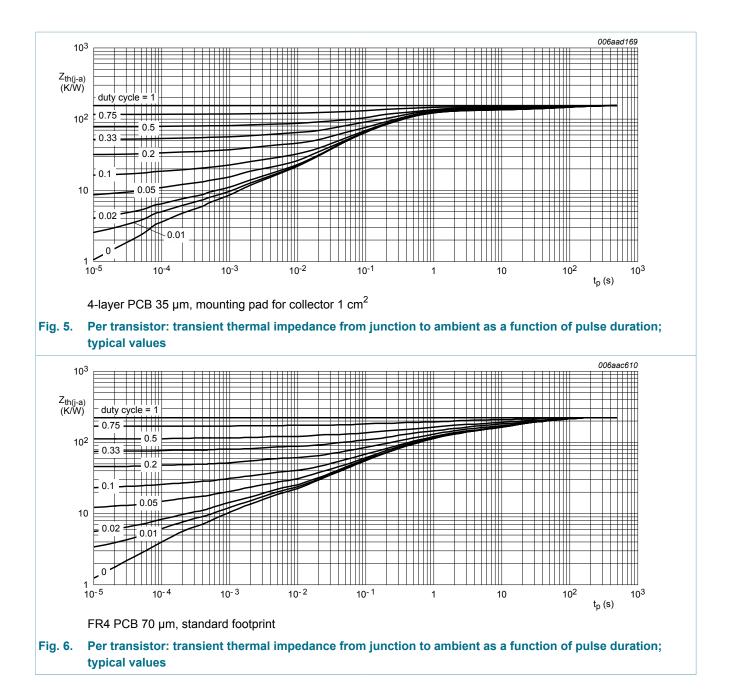
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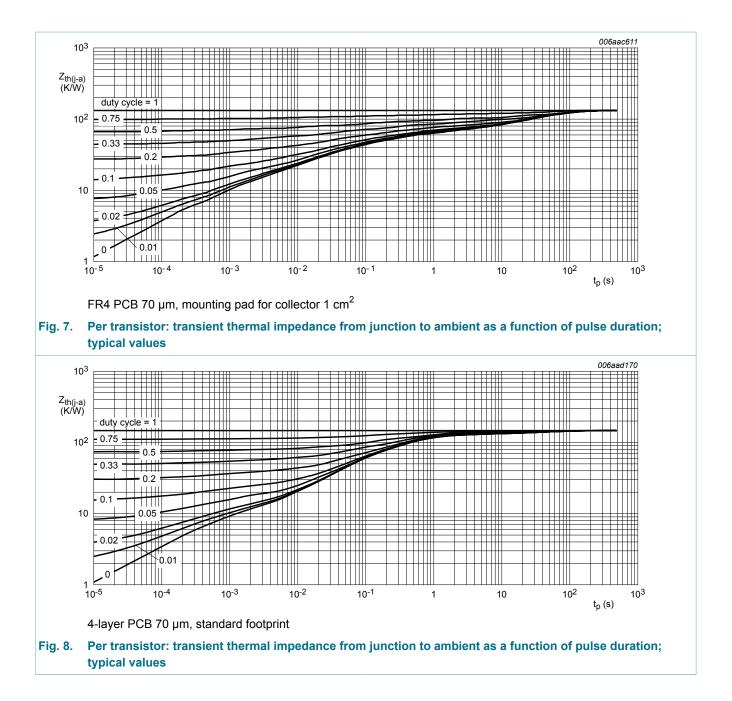


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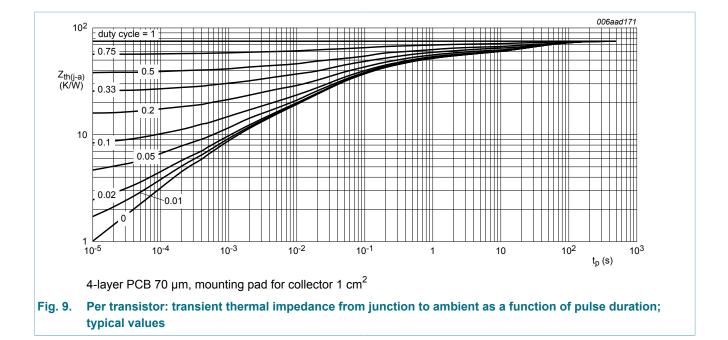


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## **10. Characteristics**

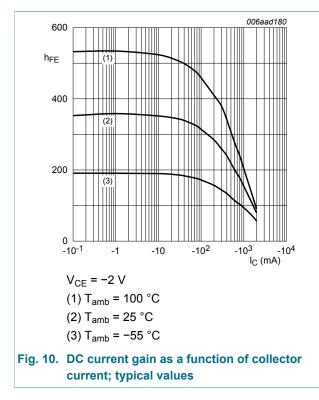
#### Table 7. Characteristics

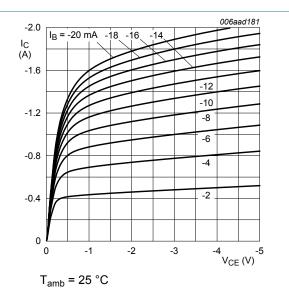
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Per transist	tor					
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -24 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	$V_{CB}$ = -24 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB}$ = -5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$\label{eq:V_CE} \begin{array}{l} V_{CE} = \text{-2 V; } I_{C} = \text{-100 mA; pulsed;} \\ t_{p} \leq 300 \ \mu s; \ \delta \leq 0.02 \ ; \ T_{amb} = 25 \ ^{\circ}C \end{array}$	250	350	-	
		$\label{eq:VcE} \begin{array}{l} V_{CE} = \text{-2 V; } I_{C} = \text{-500 mA; pulsed;} \\ t_{p} \leq 300 \ \mu s; \ \delta \leq 0.02 \ ; \ T_{amb} = 25 \ ^{\circ}C \end{array}$	170	250	-	
		$\label{eq:V_CE} \begin{array}{l} V_{CE} = \text{-2 V; } I_{C} = \text{-1 A; pulsed;} \\ t_{p} \leq 300 \; \mu s; \; \delta \leq 0.02 \; ; \; T_{amb} = 25 \; ^{\circ}C \end{array}$	120	175	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C}$ = -500 mA; $I_{B}$ = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C	-	-85	-140	mV
		$I_{C}$ = -1 A; $I_{B}$ = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C	-	-175	-280	mV
		$I_{C}$ = -1 A; $I_{B}$ = -100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C	-	-160	-250	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$\begin{split} I_{C} &= -1 \; A; \; I_{B} = -0.1 \; A; \; \text{pulsed}; \\ t_{p} &\leq 300 \; \mu s; \; \delta \leq 0.02 \; ; \; T_{amb} = 25 \; ^{\circ}\text{C} \end{split}$	-	-	250	mΩ

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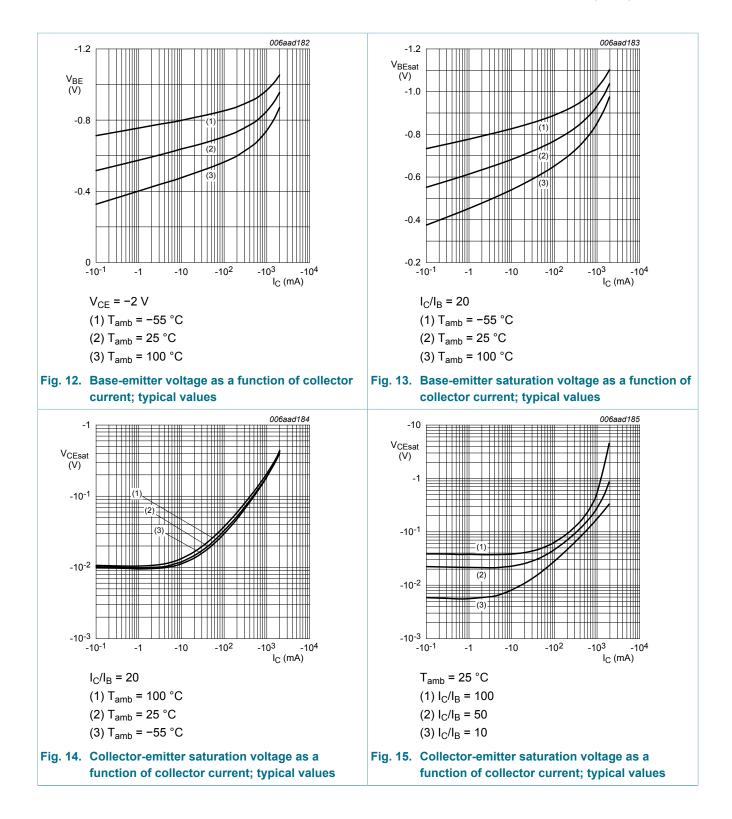
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = -500 mA; I <sub>B</sub> = -50 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02 ; T <sub>amb</sub> = 25 °C	-	-	-1	V
		$I_{C}$ = -1 A; $I_{B}$ = -50 mA; $T_{amb}$ = 25 °C	-	-	-1	V
		$I_{C}$ = -1 A; $I_{B}$ = -100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	-	-1.1	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE}$ = -2 V; I <sub>C</sub> = -0.5 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02 ; T <sub>amb</sub> = 25 °C	-	-	-0.9	V
t <sub>d</sub>	delay time	$V_{CC}$ = -10 V; I <sub>C</sub> = -0.5 A; I <sub>Bon</sub> = -25 mA;	-	15	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = 25 mA; T <sub>amb</sub> = 25 °C	-	35	-	ns
t <sub>on</sub>	turn-on time		-	50	-	ns
ts	storage time		-	105	-	ns
t <sub>f</sub>	fall time		 -	35	-	ns
t <sub>off</sub>	turn-off time		-	140	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; I <sub>C</sub> = -50 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	65	125	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	13	17	pF





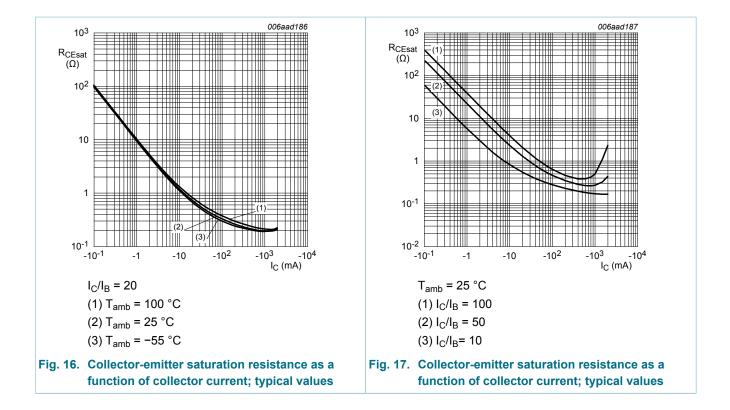


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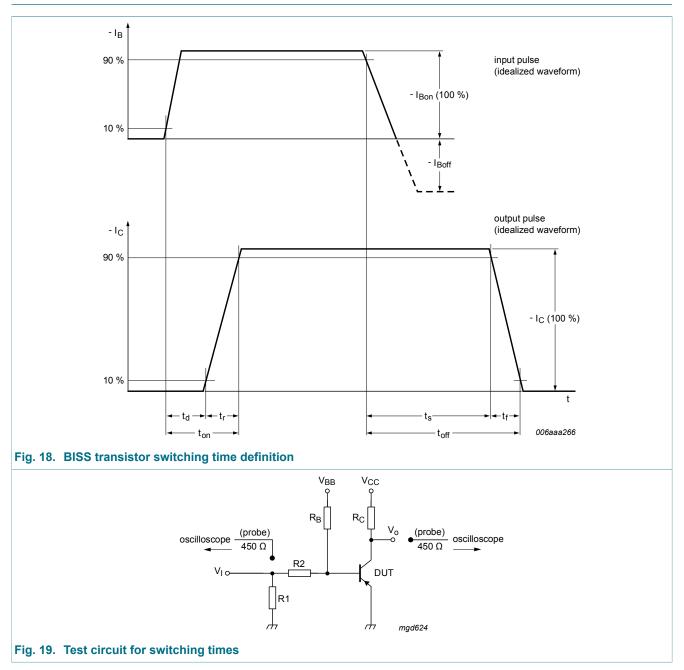


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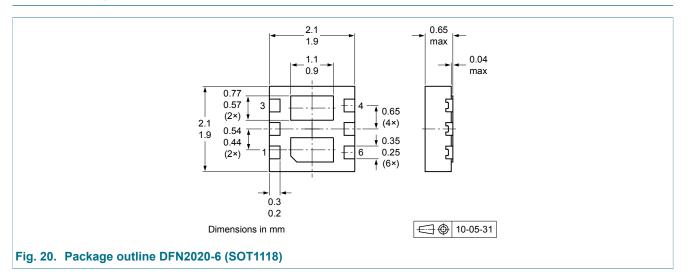
## **11. Test information**



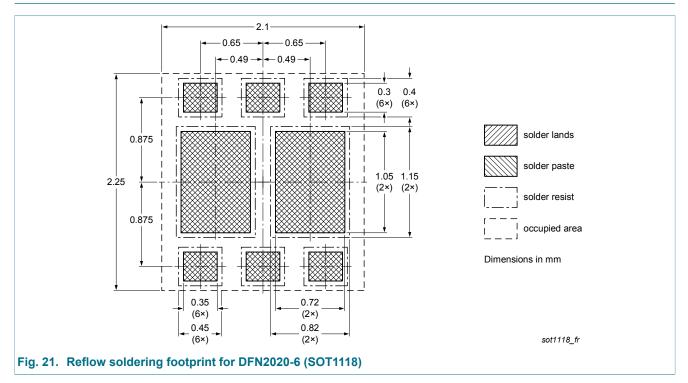
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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## 12. Package outline



## 13. Soldering



## 14. Revision history

Table 8.     Revision history								
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PBSS5130PAP v.1	20121212	Product data sheet	-	-				
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Product data sheet		12 December 2012		14 / 17				

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## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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